TOSHIBA GTR Module Silicon N Channel IGBT

MG150J2YS50

High Power Switching Applications Motor Control Applications

• The electrodes are isolated from case

• High input impedance

• Includes a complete half bridge in one package

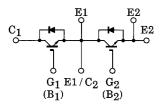
• Enhancement-mode

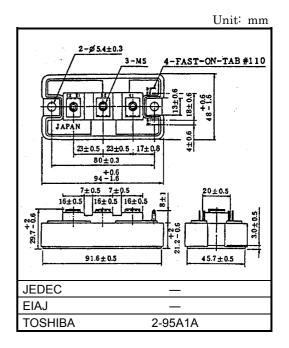
• High speed : $t_f = 0.30\mu s$ (Max) (IC = 150A)

 $t_{rr} = 0.15 \mu s \text{ (Max) (IF} = 150 \text{A)}$

• Low saturation voltage : $V_{CE (sat)} = 2.70 V (Max) (I_C = 150 A)$

Equivalent Circuit





Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	I _C	150	Α	
	1ms	I _{CP}	300		
Forward current	DC	I _F	150	Α	
	1ms	I _{FM}	300		
Collector power dissipation (Tc = 25°C)		PC	780	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

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damage to property.

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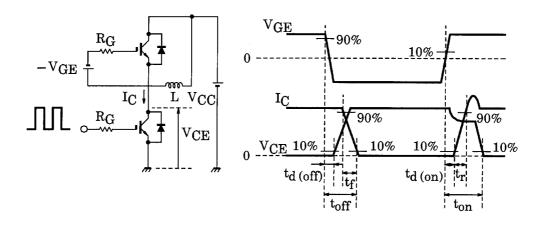
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Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ±20V, V _{CE} = 0	_	_	±500	nA
Collector cut-off current		I _{CES}	V _{CE} = 600V, V _{GE} = 0	_	_	2.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 15mA, V _{CE} = 5V	5.0	7.0	8.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 150A, V _{GE} = 15V	_	2.10	2.70	V
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz	_	14200	_	pF
Switching time	Turn-on delay time	t _{d(on)}	Inductive load $V_{CC} = 300V$ $I_{C} = 150A$ $V_{GE} = \pm 15V$ $R_{G} = 6.2\Omega$ (Note 1)	_	0.15	0.30	μs
	Rise time	t _r		_	0.15	0.30	
	Turn-on time	t _{on}		_	0.50	1.00	
	Turn-off delay time	t _{d(off)}		_	0.20	0.40	
	Fall time	t _f		_	0.15	0.30	
	Turn-off time	t _{off}		_	0.50	1.00	
Forward voltage		V _F	I _F = 150A, V _{GE} = 0	_	2.30	3.00	V
Reverse recovery time		t _{rr}	I _F = 150A, V _{GE} = -10V di / dt = 200A / μs	_	0.08	0.15	μs
Thermal resistance		R _{th (j-c)}	Transistor stage	_	_	0.16	°C/W
			Diode stage	_	_	0.35	

Note 1: Switching time test circuit & timing chart



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